

LM78S40 Universal Switching Regulator Subsystem

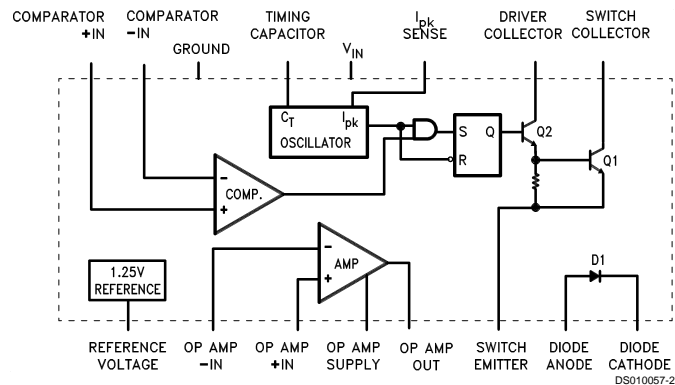
General Description

The LM78S40 is a monolithic regulator subsystem consisting of all the active building blocks necessary for switching regulator systems. The device consists of a temperature compensated voltage reference, a duty-cycle controllable oscillator with an active current limit circuit, an error amplifier, high current, high voltage output switch, a power diode and an uncommitted operational amplifier. The device can drive external NPN or PNP transistors when currents in excess of 1.5A or voltages in excess of 40V are required. The device can be used for step-down, step-up or inverting switching regulators as well as for series pass regulators. It features wide supply voltage range, low standby power dissipation, high efficiency and low drift. It is useful for any stand-alone, low part count switching system and works extremely well in battery operated systems.

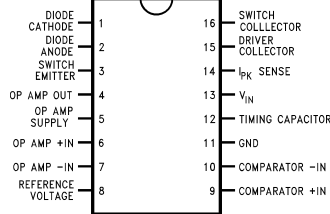
Features

- Step-up, step-down or inverting switching regulators
- Output adjustable from 1.25V to 40V
- Peak currents to 1.5A without external transistors
- Operation from 2.5V to 40V input
- Low standby current drain
- 80 dB line and load regulation
- High gain, high current, independent op amp
- Pulse width modulation with no double pulsing

Block and Connection Diagrams



16-Lead DIP



Top View

Ordering Information

Part Number	NS Package	Temperature Range
LM78S40J/883	J16A Ceramic DIP	-55°C to +125°C
LM78S40N	N16E Molded DIP	-40°C to +125°C
LM78S40CN	N16E Molded DIP	0°C to +70°C

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature Range		to GND	40V
Ceramic DIP	-65°C to +175°C	Common Mode Input Range (Comparator and Op Amp)	-0.3 to V+
Molded DIP	-65°C to +150°C	Differential Input Voltage (Note 4)	±30V
Operating Temperature Range		Output Short Circuit Duration (Op Amp)	Continuous
Extended (LM78S40J)	-55°C to +125°C	Current from V _{REF}	10 mA
Industrial (LM78S40N)	-40°C to +125°C	Voltage from Switch Collectors to GND	40V
Commercial (LM78S40CN)	0°C to +70°C	Voltage from Switch Emitters to GND	40V
Lead Temperature		Voltage from Switch Collectors to Emitter	40V
Ceramic DIP (Soldering, 60 sec.)	300°C	Voltage from Power Diode to GND	40V
Molded DIP (Soldering, 10 sec.)	265°C	Reverse Power Diode Voltage	40V
Internal Power Dissipation (Note 2) (Note 3)		Current through Power Switch	1.5A
16L-Ceramic DIP	1.50W	Current through Power Diode	1.5A
16L-Molded DIP	1.04W	ESD Susceptibility	(to be determined)
Input Voltage from V _{IN} to GND	40V		
Input Voltage from V ⁺ (Op Amp)			

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Electrical Characteristics (Note 5)

T_A = Operating temperature range, V_{IN} = 5.0V, V⁺(Op Amp) = 5.0V, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Units
GENERAL CHARACTERISTICS						
I _{CC}	Supply Current (Op Amp Disconnected)	V _{IN} = 5.0V		1.8	3.5	mA
		V _{IN} = 40V		2.3	5.0	mA
I _{CC}	Supply Current (Op Amp Connected)	V _{IN} = 5.0V			4.0	mA
		V _{IN} = 40V			5.5	mA
REFERENCE SECTION						
V _{REF}	Reference Voltage	I _{REF} = 1.0 mA Extend -55°C < T _A < +125°C, Comm 0 < T _A < +70°C, Indus -40°C < T _A < +85°C	1.180	1.245	1.310	V
V _{R LINE}	Reference Voltage Line Regulation	V _{IN} = 3.0V to V _{IN} = 40V, I _{REF} = 1.0 mA, T _A = 25°C		0.04	0.2	mV/V
V _{R LOAD}	Reference Voltage Load Regulation	I _{REF} = 1.0 mA to I _{REF} = 10 mA, T _A = 25°C		0.2	0.5	mV/mA
OSCILLATOR SECTION						
I _{CHG}	Charging Current	V _{IN} = 5.0V, T _A = 25°C	20		50	μA
I _{CHG}	Charging Current	V _{IN} = 40V, T _A = 25°C	20		70	μA
I _{DISCHG}	Discharge Current	V _{IN} = 5.0V, T _A = 25°C	150		250	μA
I _{DISCHG}	Discharge Current	V _{IN} = 40V, T _A = 25°C	150		350	μA
V _{OSC}	Oscillator Voltage Swing	V _{IN} = 5.0V, T _A = 25°C		0.5		V
t _{on} /t _{off}	Ratio of Charge/Discharge Time			6.0		μs/μs
CURRENT LIMIT SECTION						
V _{CLS}	Current Limit Sense Voltage	T _A = 25°C	250		350	mV
OUTPUT SWITCH SECTION						
V _{SAT 1}	Output Saturation Voltage 1	I _{SW} = 1.0A (Figure 1)		1.1	1.3	V
V _{SAT 2}	Output Saturation Voltage 2	I _{SW} = 1.0A (Figure 2)		0.45	0.7	V

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Electrical Characteristics (Note 5) (Continued)

T_A = Operating temperature range, V_{IN} = 5.0V, V^+ (Op Amp) = 5.0V, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OUTPUT SWITCH SECTION						
h_{FE}	Output Transistor Current Gain	$I_C = 1.0A, V_{CE} = 5.0V, T_A = 25^\circ C$		70		
I_L	Output Leakage Current	$V_O = 40V, T_A = 25^\circ C$		10		nA
POWER DIODE						
V_{FD}	Forward Voltage Drop	$I_D = 1.0A$		1.25	1.5	V
I_{DR}	Diode Leakage Current	$V_D = 40V, T_A = 25^\circ C$		10		nA
COMPARATOR						
V_{IO}	Input Offset Voltage	$V_{CM} = V_{REF}$		1.5	15	mV
I_{IB}	Input Bias Current	$V_{CM} = V_{REF}$		35	200	nA
I_{IO}	Input Offset Current	$V_{CM} = V_{REF}$		5.0	75	nA
V_{CM}	Common Mode Voltage Range	$T_A = 25^\circ C$	0		$V_{IN}-2$	V
PSRR	Power Supply Rejection Ratio	$V_{IN} = 3.0V$ to 40V, $T_A = 25^\circ C$	70	96		dB
OPERATIONAL AMPLIFIER						
V_{IO}	Input Offset Voltage	$V_{CM} = 2.5V$		4.0	15	mV
I_{IB}	Input Bias Current	$V_{CM} = 2.5V$		30	200	nA
I_{IO}	Input Offset Current	$V_{CM} = 2.5V$		5.0	75	nA
A_{VS}^+	Voltage Gain ⁺	$R_L = 2.0\text{ k}\Omega$ to GND; $V_O = 1.0V$ to 2.5V, $T_A = 25^\circ C$	25	250		V/mV
A_{VS}^-	Voltage Gain ⁻	$R_L = 2.0\text{ k}\Omega$ to V^+ (Op Amp) $V_O = 1.0V$ to 2.5V, $T_A = 25^\circ C$	25	250		V/mV
V_{CM}	Common Mode Voltage Range	$T_A = 25^\circ C$	0		$V_{CC} - 2$	V
CMR	Common Mode Rejection	$V_{CM} = 0V$ to 3.0V, $T_A = 25^\circ C$	76	100		dB
PSRR	Power Supply Rejection Ratio	V^+ (Op Amp) = 3.0V to 40V, $T_A = 25^\circ C$	76	100		dB
I_{O}^+	Output Source Current	$T_A = 25^\circ C$	75	150		mA
I_{O}^-	Output Sink Current	$T_A = 25^\circ C$	10	35		mA
SR	Slew Rate	$T_A = 25^\circ C$		0.6		V/ μ s
V_{OL}	Output Voltage LOW	$I_L = -5.0\text{ mA}, T_A = 25^\circ C$			1.0	V
V_{OH}	Output Voltage High	$I_L = 50\text{ mA}, T_A = 25^\circ C$		V^+ (Op Amp) – 3V		V

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Electrical specifications do not apply when ordering the device beyond its rated operating conditions.

Note 2: $T_{J\text{ Max}} = 150^\circ C$ for the Molded DIP, and $175^\circ C$ for the Ceramic DIP.

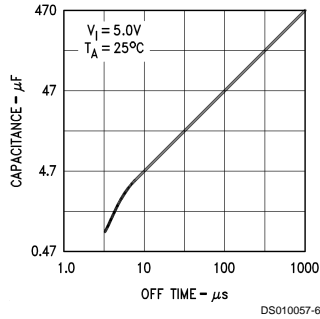
Note 3: Ratings apply to ambient temperature at $25^\circ C$. Above this temperature, derate the 16L-Ceramic DIP at $10\text{ mW}/^\circ C$, and the 16L-Molded DIP at $8.3\text{ mW}/^\circ C$.

Note 4: For supply voltages less than 30V, the absolute maximum voltage is equal to the supply voltage.

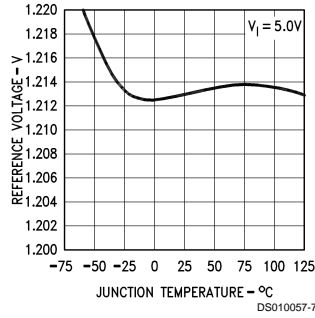
Note 5: A military RETS specification is available on request. At the time of printing, the LM78S40 RETS specification complied with the Min and Max limits in this table. The LM78S40J may also be procured as a Standard Military Drawing.

Typical Performance Characteristics

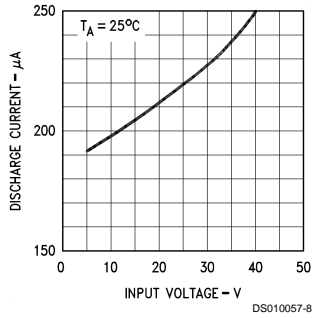
C_T vs OFF Time



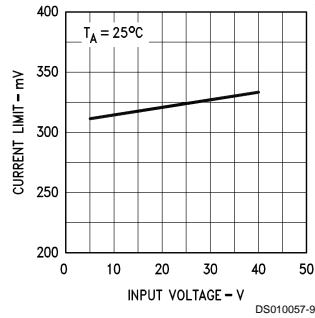
Reference Voltage vs Junction Temperature



Discharge Current vs Input Voltage



Current Limit Sense Voltage vs Input Voltage

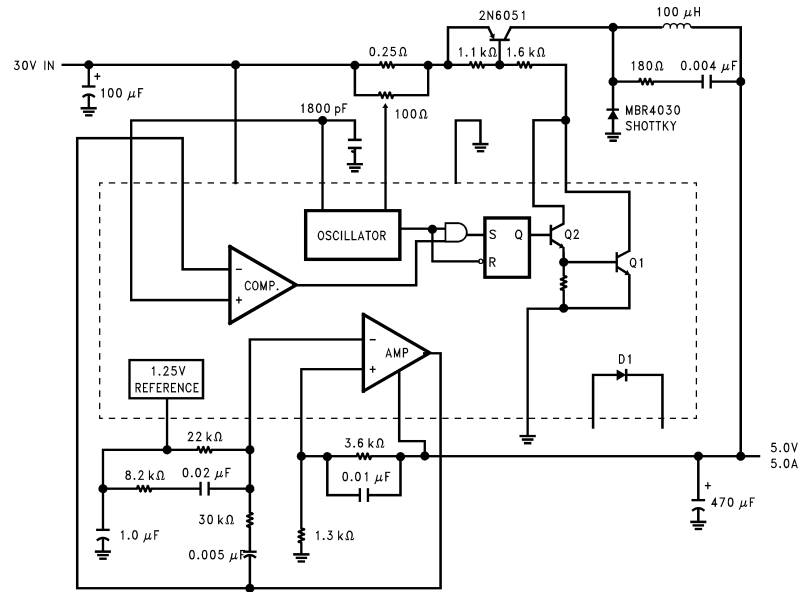


Design Formulas

Characteristic	Step-Down	Step-Up	Inverting	Units
$\frac{t_{on}}{t_{off}}$	$\frac{V_O + V_D}{V_I - V_{SAT} - V_O}$	$\frac{V_O + V_D - V_I}{V_I - V_{SAT}}$	$\frac{ V_O + V_D}{V_I - V_{SAT}}$	
$(t_{on} + t_{off})_{Max}$	$\frac{1}{f_{Min}}$	$\frac{1}{f_{Min}}$	$\frac{1}{f_{MIN}}$	μs
C_T	$4 \times 10^{-5} t_{on}$	$4 \times 10^{-5} t_{on}$	$4 \times 10^{-5} t_{on}$	μF
I_{pk}	$2 I_{O Max}$	$2 I_{O Max} \cdot \frac{t_{on} + t_{off}}{t_{off}}$	$2 I_{O Max} \cdot \frac{t_{on} + t_{off}}{t_{off}}$	A
L_{Min}	$\left(\frac{V_I - V_{SAT} - V_O}{I_{pk}} \right) t_{on Max}$	$\left(\frac{V_I - V_{SAT}}{I_{pk}} \right) t_{on Max}$	$\left(\frac{V_I - V_{SAT}}{I_{pk}} \right) t_{on Max}$	μH
R_{SC}	$0.33/I_{pk}$	$0.33/I_{pk}$	$0.33/I_{pk}$	Ω
C_O	$\frac{I_{pk} (t_{on} + t_{off})}{8 V_{ripple}}$	$\approx \frac{I_O}{V_{ripple}} \cdot t_{on}$	$\approx \frac{I_O}{V_{ripple}} \cdot t_{on}$	μF

Note 6: V_{SAT} = Saturation voltage of the switching element.
 V_D = Forward voltage of the flyback diode.

Typical Applications (Continued)



DS010057-10

FIGURE 4. Pulse Width Modulated Step-Down Regulator ($f_{OSC} = 20 \text{ kHz}$)

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